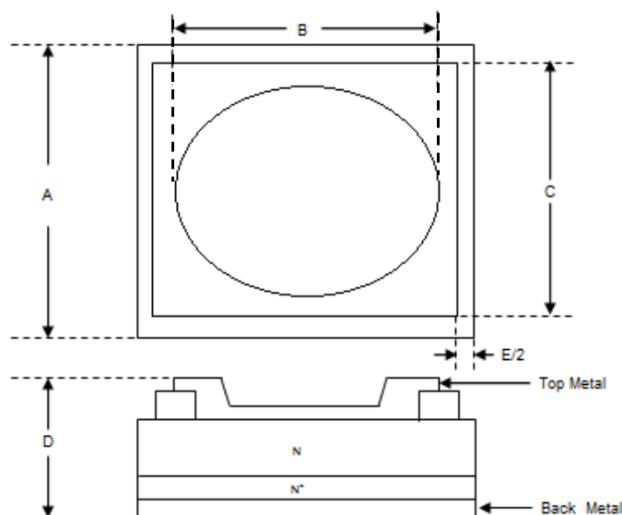


Planar Schottky Barrier Diode Wafer (PSBD)



Item	Dimensions	
	um	mil
Die Size (A)	230	9
Top Metal Pad Size (B)	109	4.29
Passivation Seal (C)	185	7.28
Wafer Thickness (D)	153	6
Scribe Line Width (E)	45	1.77
Other Informations		
Wafer Size	6"	
Gross Die	300200	
Top Metal	Al	
Back Metal	Ag	

Electrical Characteristics @TA=25°C

Item	Symbol	Spec. Limit	Die Sort	Unit
Maximum Repetitive Peak Reverse Voltage @0.25mA	V_{RRM}	100	-	V
Maximum Average Forward Rectified Current	I_o	0.1	-	A
Forward Voltage Drop, @ $I_F=1mA$ @ $I_F=10mA$ @ $I_F=50mA$ @ $I_F=150mA$	V_F	0.70 0.85 0.98 1.18	-	V
Maximum Reverse Current @ $V_R=20V$ @ $V_R=75V$ @ $V_R=100V$	I_R	0.02 0.60 1.00	-	μA
Reverse Recovery Time $I_F=10mA$, $I_R=1mA$, $V_R=6V$, $R_L=100\Omega$	T_{RR}	4	-	nS
Operating Temperature Range	T_J	-50 to +175	-	°C
Storage Temperature Range	T_{STG}	-50 to +175	-	°C